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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the application of: **Y. INOUE et al.**

Serial No.: 08/921,250

Filed: August 29, 1997

For: **FABRICATION METHOD OF SEMICONDUCTOR DEVICE AND ABRASIVE LIQUID USED THEREIN**



PATENT APPLICATION

Art Uni

Examiner: G. Gou

AMENDMENT TRANSMITTAL

Director of Patents and Trademarks
Washington, D.C. 20231

October 17, 2000

Sir:

Transmitted herewith is an Amendment in the above-identified application.

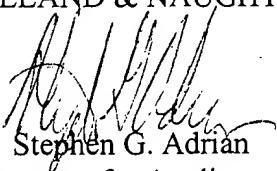
- Small Entity status of this application under 37 CFR 1.9 and 1.27 has been established by a verified statement previously submitted.
 - A verified statement to establish Small Entity status under 37 CFR 1.9 and 1.27 is enclosed.

The fee has been calculated as shown below:

The Commissioner is hereby authorized to charge payment for any additional fees associated with this communication or credit any overpayment to Deposit Account No. 01-2340. Two duplicates of this sheet are attached.

Respectfully submitted,

ARMSTRONG, WESTERMAN, HATTORI,
McLELAND & NAUGHTON



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AMENDMENT

Director of Patents and Trademarks
Washington, D.C. 20231

Sir:

In response to the Office Action dated July 18, 2000, please amend the above-identified application as follows:

IN THE CLAIMS:

Please amend claims 3, 4, 7-11, 13, 17, 18 and 26 as follows:

Claim 3, line 1, change "8" to --32--; and

line 2, change "planrization" to --planarization--.

Claim 4, line 1, change "8" to --32--.

6 *7*. (Twice Amended) [A] The fabrication method of a semiconductor device according to
claim 3, further comprising the step of: [comprising the steps of:

forming a first insulation film on a substrate,

forming a second insulation film on said first insulation film,